

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MA245FK

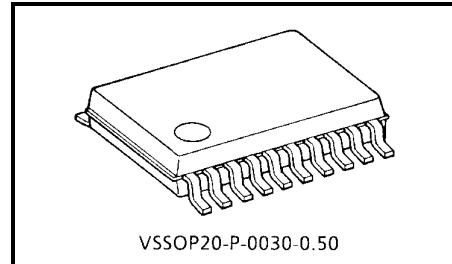
Low-Voltage Octal Bus Transceiver with 3.6 V Tolerant Inputs and Outputs

The TC7MA245FK is a high performance CMOS octal bus transceiver which is guaranteed to operate from 1.2-V to 3.6-V. Designed for use in 1.5V, 1.8V, 2.5V or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.

The direction of data transmission is determined by the level of the DIR inputs. The \overline{OE} inputs can be used to disable the device so that the busses are effectively isolated.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.03 g (typ.)

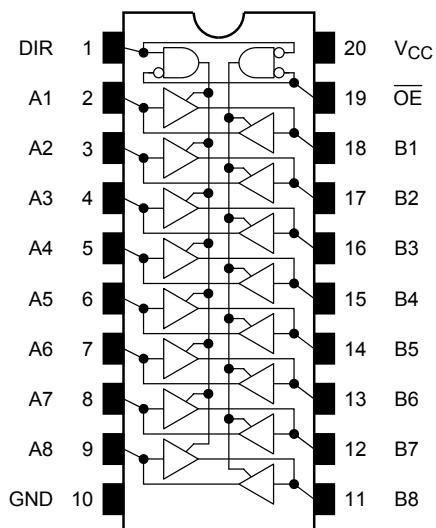
Features

- Low voltage operation: $V_{CC} = 1.2\sim 3.6$ V
- High speed operation:
 $t_{pd} = 3.5$ ns (max) ($V_{CC} = 3.0\sim 3.6$ V)
 $t_{pd} = 4.2$ ns (max) ($V_{CC} = 2.3\sim 2.7$ V)
 $t_{pd} = 8.4$ ns (max) ($V_{CC} = 1.65\sim 1.95$ V)
 $t_{pd} = 16.8$ ns (max) ($V_{CC} = 1.4\sim 1.6$ V)
 $t_{pd} = 42.0$ ns (max) ($V_{CC} = 1.2$ V)
- 3.6 V tolerant inputs and outputs.
- Output current:
 $I_{OH}/I_{OL} = \pm 24$ mA (min) ($V_{CC} = 3.0$ V)
 $I_{OH}/I_{OL} = \pm 18$ mA (min) ($V_{CC} = 2.3$ V)
 $I_{OH}/I_{OL} = \pm 6$ mA (min) ($V_{CC} = 1.65$ V)
 $I_{OH}/I_{OL} = \pm 2$ mA (min) ($V_{CC} = 1.4$ V)
- Latch-up performance: -300 mA
- ESD performance: Machine model $\geq \pm 200$ V
Human body model $\geq \pm 2000$ V
- Package: VSSOP(US)
- Bidirectional interface between 2.5 V and 3.3 V signals. (*1)
- Power down protection is provided on all inputs and outputs. (*2)

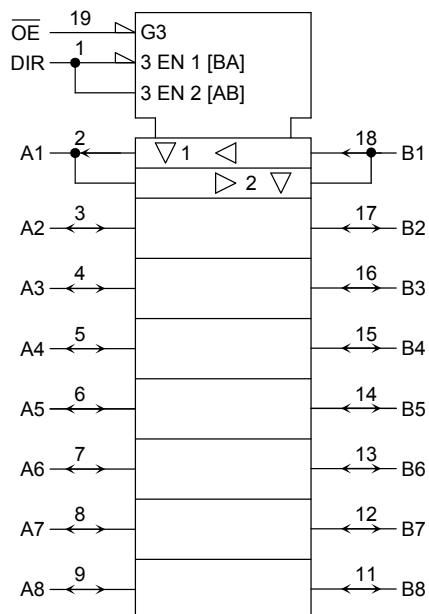
*1: Do not apply a signal to any bus terminal when it is in the output mode. Damage may result.

*2: All floating (high impedance) bus terminal must have their input level fixed by means of pull up or pull down resistors.

Pin Assignment (top view)



IEC Logic Symbol



Truth Table

Inputs		Outputs	Function	
OE-bar	DIR		A-Bus	B-Bus
L	L	A = B	Output	Input
L	H	B = A	Input	Output
H	X	Z		Z

X: Don't care

Z: High impedance

Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5~4.6	V
DC input voltage (DIR, OĒ)	V _{IN}	-0.5~4.6	V
DC bus I/O voltage	V _{I/O}	-0.5~4.6 (Note 2)	V
		-0.5~V _{CC} + 0.5 (Note 3)	
Input diode current	I _{IK}	-50	mA
Output diode current	I _{OK}	±50 (Note 4)	mA
DC output current	I _{OUT}	±50	mA
Power dissipation	P _D	180	mW
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65~150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: V_{CC} = 0 V

Note 3: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 4: V_{OUT} < GND, V_{OUT} > V_{CC}

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	1.2~3.6	V
Input voltage (DIR, OĒ)	V _{IN}	-0.3~3.6	V
Bus I/O voltage	V _{I/O}	0~3.6 (Note 2)	V
		0~V _{CC} (Note 3)	
Output current	I _{OH} /I _{OL}	±24 (Note 4)	mA
		±18 (Note 5)	
		±6 (Note 6)	
		±2 (Note 7)	
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	d _t /d _v	0~10 (Note 8)	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs and bus inputs must be tied to either V_{CC} or GND. Please connect both bus inputs and the bus outputs with V_{CC} or GND when the I/O of the bus terminal changes by the function. In this case, please note that the output is not short-circuited.

Note 2: Off-state

Note 3: High or low state

Note 4: V_{CC} = 3.0~3.6 V

Note 5: V_{CC} = 2.3~2.7 V

Note 6: V_{CC} = 1.65~1.95 V

Note 7: V_{CC} = 1.4~1.6 V

Note 8: V_{IN} = 0.8~2.0 V, V_{CC} = 3.0 V

Electrical Characteristics**DC Characteristics (Ta = -40~85°C, 2.7 V < V_{CC} ≤ 3.6 V)**

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Input voltage	High level		—	2.7~3.6					
	Low level	V _{IL}	—	2.7~3.6	—	0.8	—		
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.7~3.6	V _{CC} - 0.2	—	V	
				I _{OH} = -12 mA	2.7	2.2	—		
				I _{OH} = -18 mA	3.0	2.4	—		
				I _{OH} = -24 mA	3.0	2.2	—		
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7~3.6	—	0.2		
				I _{OL} = 12 mA	2.7	—	0.4		
				I _{OL} = 18 mA	3.0	—	0.4		
				I _{OL} = 24 mA	3.0	—	0.55		
Input leakage current	I _{IN}	V _{IN} = 0~3.6 V			2.7~3.6	—	±5.0	μA	
3-state output off-state current	I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V			2.7~3.6	—	±10.0	μA	
Power off leakage current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V			0	—	10.0	μA	
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V			2.7~3.6	—	20.0	μA	
Increase in I _{CC} per input	ΔI _{CC}	V _{IH} = V _{CC} - 0.6 V			2.7~3.6	—	750		

DC Characteristics (Ta = -40~85°C, 2.3 V ≤ V_{CC} ≤ 2.7 V)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Input voltage	High level		—	2.3~2.7					
	Low level	V _{IL}	—	2.3~2.7	—	0.7	—		
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	—	V	
				I _{OH} = -6 mA	2.3	2.0	—		
				I _{OH} = -12 mA	2.3	1.8	—		
				I _{OH} = -18 mA	2.3	1.7	—		
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.3~2.7	—	0.2		
				I _{OL} = 12 mA	2.3	—	0.4		
				I _{OL} = 18 mA	2.3	—	0.6		
				I _{OL} = 24 mA	2.3	—	0.6		
Input leakage current	I _{IN}	V _{IN} = 0~3.6 V			2.3~2.7	—	±5.0	μA	
3-state output off-state current	I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V			2.3~2.7	—	±10.0	μA	
Power off leakage current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V			0	—	10.0	μA	
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V			2.3~2.7	—	20.0	μA	
Increase in I _{CC} per input		V _{IH} = V _{CC} - 0.6 V			2.3~2.7	—	±20.0		

DC Characteristics (Ta = -40~85°C, 1.65 V ≤ V_{CC}< 2.3 V)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Input voltage	High level	V _{IH}	—		1.65~2.3	0.65 × V _{CC}	—	V
	Low level	V _{IL}	—		1.65~2.3	—	0.2 × V _{CC}	
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA I _{OH} = -6 mA	1.65~2.3 1.65	V _{CC} - 0.2 1.25	—	V
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA I _{OL} = 6 mA	1.65~2.3 1.65	—	0.2 0.3	
Input leakage current	I _{IN}	V _{IN} = 0~3.6 V		—		1.65~2.3	—	±5.0 μA
3-state output off-state current	I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V		—		1.65~2.3	—	±10.0 μA
Power off leakage current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		—		0	—	10.0 μA
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND		—		1.65~2.3	—	20.0 μA
		V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		—		1.65~2.3	—	±20.0 μA

DC Characteristics (Ta = -40~85°C, 1.4 V ≤ V_{CC}< 1.65 V)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Input voltage	High level	V _{IH}	—		1.4~1.65	0.65 × V _{CC}	—	V	
	Low level	V _{IL}	—		1.4~1.65	—	0.05 × V _{CC}		
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA I _{OH} = -2 mA	1.4~1.65 1.4	V _{CC} - 0.2 1.05	—	V	
	Low level	V _{OL}		I _{OL} = 100 μA I _{OL} = 2 mA	1.4~1.65 1.4	—	0.05 0.35		
Input leakage current	I _{IN}	V _{IN} = 0~3.6 V		—		1.4~1.65	—	±5.0 μA	
3-state output off-state current	I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V		—		1.4~1.65	—	±10.0 μA	
Power off leakage current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		—		0	—	10.0 μA	
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND		—		1.4~1.65	—	20.0 μA	
		V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		—		1.4~1.65	—	±20.0 μA	

DC Characteristics ($T_a = -40\text{~}85^\circ\text{C}$, $1.2 \text{ V} \leq V_{CC} < 1.4 \text{ V}$)

Characteristics		Symbol	Test Condition		$V_{CC} (\text{V})$	Min	Max	Unit	
Input voltage	High level	V_{IH}	—			1.2~1.4	$0.8 \times V_{CC}$	—	
	Low level	V_{IL}	—			1.2~1.4	—	$0.05 \times V_{CC}$	
Output voltage	High level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100 \mu\text{A}$	1.2	$V_{CC} - 0.1$	—	V	
	Low level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu\text{A}$	1.2	—	0.05	V	
Input leakage current	I_{IN}	$V_{IN} = 0\text{~}3.6 \text{ V}$		—	1.2	—	± 5.0	μA	
3-state output off-state current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0\text{~}3.6 \text{ V}$		—	1.2	—	± 10.0	μA	
Power off leakage current	I_{OFF}	$V_{IN}, V_{OUT} = 0\text{~}3.6 \text{ V}$		—	0	—	10.0	μA	
Quiescent supply current	I_{CC}	$V_{IN} = V_{CC}$ or GND		—	1.2	—	20.0	μA	
		$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		—	1.2	—	± 20.0		

AC Characteristics ($T_a = -40\text{~}85^\circ\text{C}$, Input: $t_r = t_f = 2.0 \text{ ns}$, $C_L = 30 \text{ pF}$, $R_L = 500 \Omega$)

Characteristics		Symbol	Test Condition		$V_{CC} (\text{V})$	Min	Max	Unit
Propagation delay time	t_{pLH} t_{pHL}	Figure 1, Figure 2	$C_L = 15 \text{ pF}, R_L = 2 \text{ k}\Omega$	1.2		1.5	42.0	ns
				1.5 ± 0.1		1.0	16.8	
			$C_L = 30 \text{ pF}, R_L = 500 \Omega$	1.8 ± 0.15		1.5	8.4	
				2.5 ± 0.2		0.8	4.2	
				3.3 ± 0.3		0.6	3.5	
3-state output enable time	t_{pZL} t_{pZH}	Figure 1, Figure 3	$C_L = 15 \text{ pF}, R_L = 2 \text{ k}\Omega$	1.2		1.5	49.0	ns
				1.5 ± 0.1		1.0	19.6	
			$C_L = 30 \text{ pF}, R_L = 500 \Omega$	1.8 ± 0.15		1.5	9.8	
				2.5 ± 0.2		0.8	5.6	
				3.3 ± 0.3		0.6	4.5	
3-state output disable time	t_{pLZ} t_{pHZ}	Figure 1, Figure 3	$C_L = 15 \text{ pF}, R_L = 2 \text{ k}\Omega$	1.2		1.5	36.0	ns
				1.5 ± 0.1		1.0	14.4	
			$C_L = 30 \text{ pF}, R_L = 500 \Omega$	1.8 ± 0.15		1.5	7.2	
				2.5 ± 0.2		0.8	4.0	
				3.3 ± 0.3		0.6	3.6	
Output to output skew	t_{osLH} t_{osHL}	(Note)	$C_L = 15 \text{ pF}, R_L = 2 \text{ k}\Omega$	1.2		—	1.5	ns
				1.5 ± 0.1		—	1.5	
			$C_L = 30 \text{ pF}, R_L = 500 \Omega$	1.8 ± 0.15		—	0.5	
				2.5 ± 0.2		—	0.5	
				3.3 ± 0.3		—	0.5	

For $C_L = 50 \text{ pF}$, add approximately 300 ps to the AC maximum specification.

Note: This parameter is guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

Dynamic Switching Characteristics (Ta = 25°C, Input: t_r = t_f = 2.0 ns, C_L = 30 pF)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Quiet output maximum dynamic V _{OL}	V _{O LP}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note)	1.8	0.25	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note)	2.5	0.6	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note)	3.3	0.8	
Quiet output minimum dynamic V _{OL}	V _{O LV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note)	1.8	-0.25	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note)	2.5	-0.6	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note)	3.3	-0.8	
Quiet output minimum dynamic V _{OH}	V _{O HV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note)	1.8	1.5	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note)	2.5	1.9	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note)	3.3	2.2	

Note: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

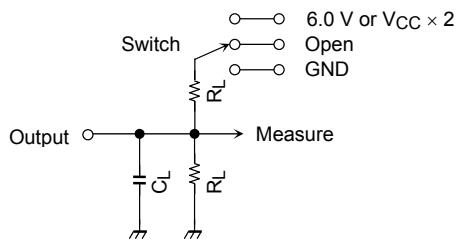
Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Input capacitance	C _{IN}	—	1.8, 2.5, 3.3	6	pF
Bus I/O capacitance	C _{I/O}	—	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz (Note)	1.8, 2.5, 3.3	20	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$$

AC Test Circuit

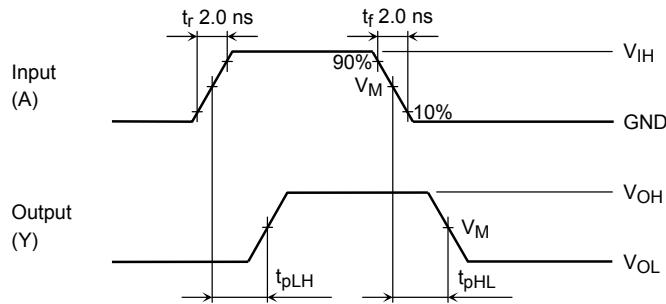


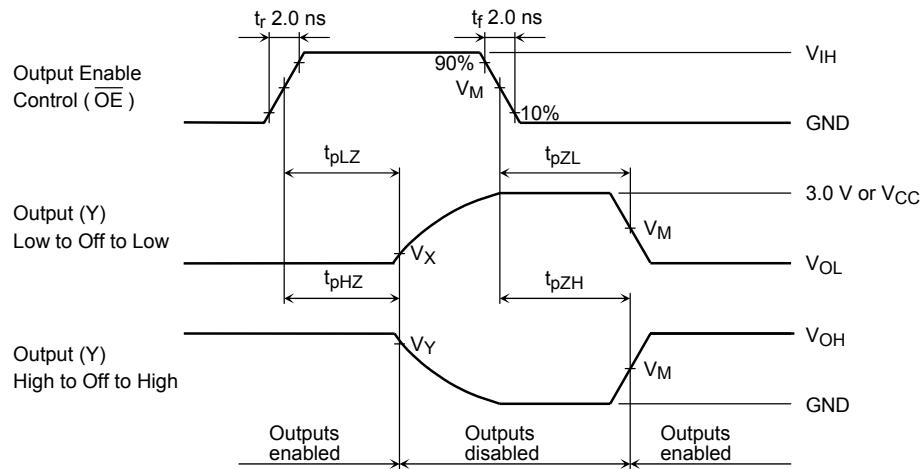
Parameter	Switch
t_{pLH}, t_{pHL}	Open
t_{pLZ}, t_{pZL}	6.0 V $V_{CC} \times 2$ @ $V_{CC} = 3.3 \pm 0.3$ V @ $V_{CC} = 2.5 \pm 0.2$ V @ $V_{CC} = 1.8 \pm 0.15$ V @ $V_{CC} = 1.5 \pm 0.1$ V @ $V_{CC} = 1.2$ V
t_{pHZ}, t_{pZH}	GND

Symbol	V_{CC}	
	3.3 \pm 0.3 V 2.5 \pm 0.2 V 1.8 \pm 0.15 V	1.5 \pm 0.1 V 1.2 V
R_L	500 Ω	2k Ω
C_L	30pF	15pF

Figure 1

AC Waveform

Figure 2 t_{pLH}, t_{pHL}

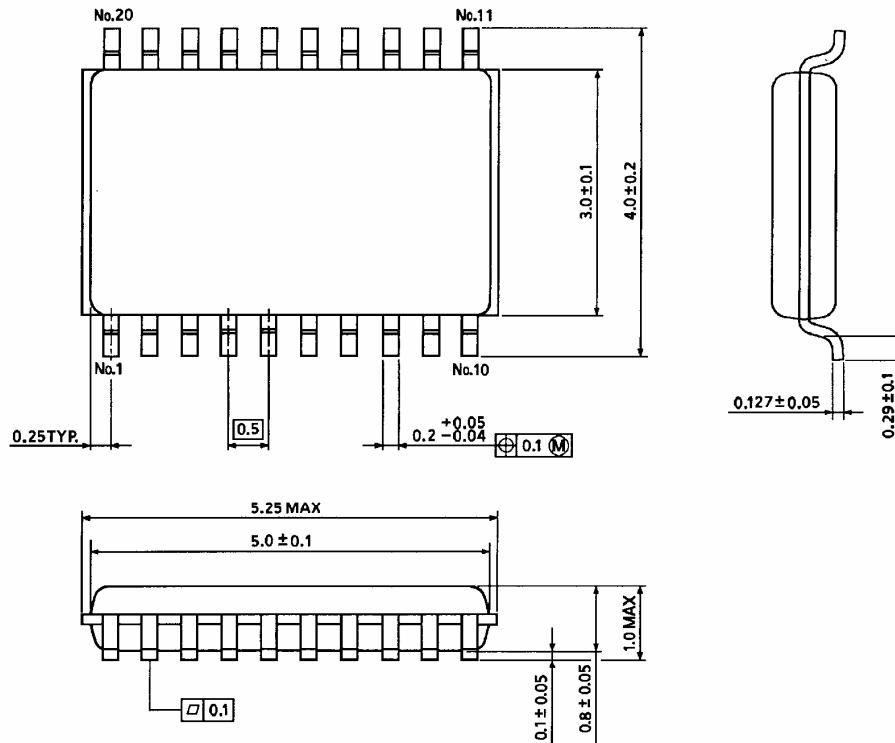
Figure 3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

Symbol	V_{CC}				
	$3.3 \pm 0.3\text{ V}$	$2.5 \pm 0.2\text{ V}$	$1.8 \pm 0.15\text{ V}$	$1.5 \pm 0.1\text{ V}$	1.2 V
V_{IH}	2.7 V	V_{CC}	V_{CC}	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$
V_X	$V_{OL} + 0.3\text{ V}$	$V_{OL} + 0.15\text{ V}$	$V_{OL} + 0.15\text{ V}$	$V_{OL} + 0.1\text{ V}$	$V_{OL} + 0.1\text{ V}$
V_Y	$V_{OH} - 0.3\text{ V}$	$V_{OH} - 0.15\text{ V}$	$V_{OH} - 0.15\text{ V}$	$V_{OH} - 0.1\text{ V}$	$V_{OH} - 0.1\text{ V}$

Package Dimensions

VSSOP20-P-0030-0.50

Unit : mm



Weight: 0.03 g (typ.)

RESTRICTIONS ON PRODUCT USE

20070701-EN

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